

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application.

**Listing of Claims:**

Claim 1 (Currently amended): A method for removing particles on semiconductor wafers, comprising the steps of:

performing a first cleaning process in which semiconductor wafers are cleaned for a prescribed time by immersing them in a first cleaning solution consisting of ultra-pure water containing a prescribed quantity of ozone in a first cleaning tank; and

performing a second cleaning process in which said semiconductor wafers are cleaned for a prescribed time by immersing them in a second cleaning solution consisting of ultra-pure water containing ~~a prescribed quantity~~ 0.3 ppm to 0.499 ppm of hydrogen in a second cleaning tank, wherein ultrasonic waves are supplied to said second cleaning solution in said second process.

Claim 2 (original): A method for removing particles on semiconductor wafers as described in claim 1, further comprising the step of, between said first cleaning process and said second cleaning process, performing a third cleaning process in which said semiconductor wafers are cleaned for a prescribed time by immersing them in a third cleaning solution consisting of ultra-pure water in a third cleaning tank.

Claim 3 (original): A method for removing particles on semiconductor wafers as described in claim 1, further comprising the step of, after said second cleaning process, performing a fourth cleaning process in which said semiconductor wafers are cleaned for a prescribed time by immersing them in a fourth cleaning solution consisting of HF mixed solution in a fourth cleaning tank.

Claim 4 (Currently canceled)

Claim 5 (original): A method for removing particles on semiconductor wafers as described in claim 1, wherein an in-solution concentration of ozone in said first cleaning solution is in the range 2 ppm to 20 ppm.

Claim 6 (Currently canceled)

Claim 7 (Currently canceled)

Claim 8 (original): A method for removing particles on semiconductor wafers as described in claim 1, wherein the prescribed time in said first and second cleaning processes is in the range 3 to 20 minutes.

Claim 9 (withdrawn): A device for removing particles on semiconductor wafers, comprising:

a first cleaning tank filled with a first cleaning solution consisting of ultra-pure water containing a prescribed quantity of ozone;

a second cleaning tank filled with a second cleaning solution consisting of ultra-pure water containing a prescribed quantity of hydrogen;

an ultrasonic wave supply means for supplying ultrasonic waves to said second cleaning solution in said second cleaning tank; and

a control means that controls the conveyance so as to immerse the semiconductor wafers in said first cleaning solution in said first cleaning tank, after a prescribed time remove said semiconductor wafers from said first cleaning solution and immerse them in said second cleaning solution in said second cleaning, and after a prescribed time remove said semiconductor wafers from said second cleaning solution.